



Product Overview

NVMFS5833N: Power MOSFET 40V, 86A, 7.5 mOhm, Single N-Channel, SO8-FL.

For complete documentation, see the data sheet

Product Description

Automotive Power MOSFET in a 5x6mm flat lead package designed for compact and efficient designs and including high thermal performance. Wettable Flank Option available for Enhanced Optical Inspection. AEC-Q101 Qualified MOSFET and PPAP capable suitable for automotive applications.

Features

- Low RDS(on)
- AEC-Q101qualified
- 5 x 6 x 1 mm SO-8FL package
- Standard Gate Level (VTH min. = 2 V)

Benefits

- Reduced conduction losses
- Suitable for use in automotive applications
- Reduced board space, smaller modules
- Ensures turn off in noisy environments (motor control)

Applications

- Motor Control

End Products

- Engine control module
- Body control module
- Chassis control module

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	V _{DS} (BR) Min (V)	V _{GS} Max (V)	V _{GS} (th) Max (V)	I _D Max (A)	P _D Max (W)	r _{DS(on)} Max @ V _{GS} = 2.5 V (m)	r _{DS(on)} Max @ V _{GS} = 4.5 V (m)	r _{DS(on)} Max @ V _{GS} = 10 V (m)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	Q _{gd} Typ @ V _{GS} = 4.5 V (nC)	Q _{rr} Typ (nC)	C _{iss} Typ (pF)	C _{oss} Typ (pF)	C _{rss} Typ (pF)	Packaging Type
NVMFS5833NT1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	40	20	3.5	86	112			7.5		32.5		14	1714	210	144	SO-8FL / DF N-5
NVMFS5833NT3G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	40	20	3.5	86	112			7.5		32.5		14	1714	210	144	SO-8FL / DF N-5
NVMFS5833NWFT1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	40	20	3.5	86	112			7.5		32.5		14	1714	210	144	SO-8FL / DF N-5
NVMFS5833NWFT3G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	40	20	3.5	86	112			7.5		32.5		14	1714	210	144	SO-8FL / DF N-5

For more information please contact your local sales support at www.onsemi.com

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